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March 2014

FQA8N100C

N-Channel QFET® MOSFET

1000 V, 8 A, 1.45 Ω

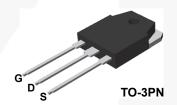
Features

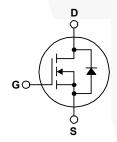
- $R_{DS(on)} = 1.45 \Omega (Max.) @ V_{GS} = 10 V, I_D = 4 A$
- Low Gate Charge (Typ. 53 nC)
- Low Crss (Typ. 16 pF)
- · 100% Avalanche Tested

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA8N100C	Unit	
V _{DSS}	Drain-Source Voltage		1000	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)		8 5	A A	
I _{DM}	Drain Current - Pulsed	(Note 1)	32	Α	
V _{GSS}	Gate-Source voltage		±30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	850	mJ	
I _{AR}	Avalanche Current	(Note 1)	8	Α	
E _{AR}	Repetitive Avalanche Energy (22.5	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns	
P_{D}	Power Dissipation (T _C = 25°C) - Derate above 25°C		225 1.79	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQA8N100C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.56	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA8N100C	FQA8N100C	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics			ı		
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	1000			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		1.4		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 1000V, V _{GS} = 0V V _{DS} = 800V, T _C = 125°C			10 100	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	-		100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	teristics			•		
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 4A		1.2	1.45	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50V, I _D = 4A		8.0		S
Dynamic C	haracteristics			•		
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V,	\	2475	3220	pF
C _{oss}	Output Capacitance	f = 1.0MHz		195	255	pF
C _{rss}	Reverse Transfer Capacitance			16	24	pF
Switching	Characteristics				_	
t _{d(on)}	Turn-On Delay Time	V _{DD} = 500V, I _D = 8A		50	110	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$		95	200	ns
t _{d(off)}	Turn-Off Delay Time			122	254	ns
t _f	Turn-Off Fall Time	(Note 4)		80	170	ns
Qg	Total Gate Charge	V _{DS} = 800V, I _D = 8A	/	53	70	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V	/	13		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	7-	23		nC
Drain-Sour	rce Diode Characteristics and Maximur	m Ratings	Á	I	7	
I _S	Maximum Continuous Drain-Source Diode Forward Current				8	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				32	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 8A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 8A		620		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs		5.2		μС

NOTES

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 25 mH, I $_{AS}$ = 8 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$

 $^{3.}I_{SD} \leq 8 \text{ A, di/dt} \leq 200 \text{ A/}\mu\text{s, V}_{DD} \leq \text{BV}_{DSS}\text{, starting T}_{J} = 25^{\circ}\text{C}.$

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

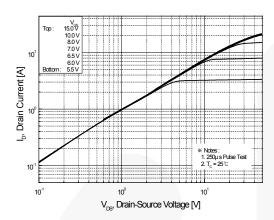


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

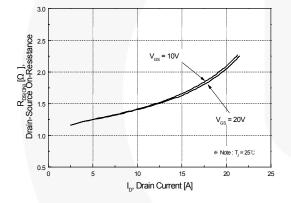


Figure 2. Transfer Characteristics

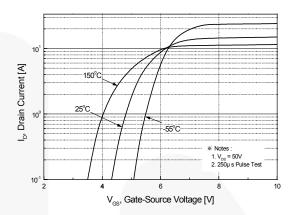


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

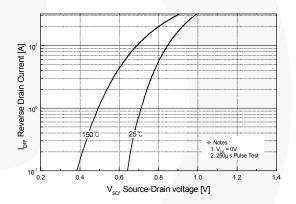


Figure 5. Capacitance Characteristics

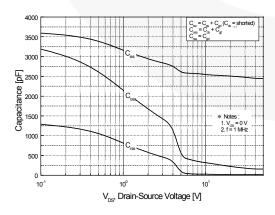
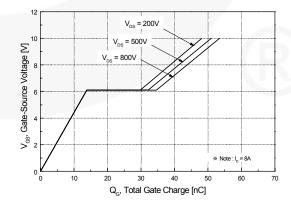


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

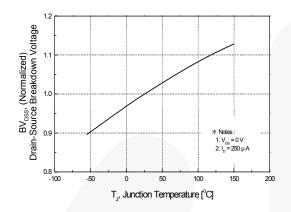


Figure 8. On-Resistance Variation vs. Temperature

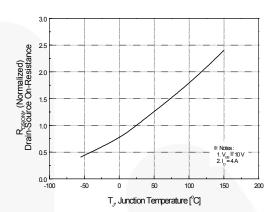


Figure 9. Maximum Safe Operating Area

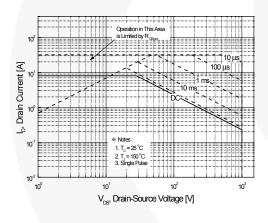


Figure 10. Maximum Drain Current vs. Case Temperature

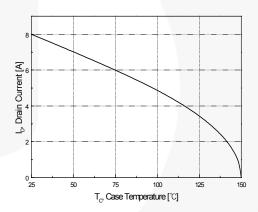
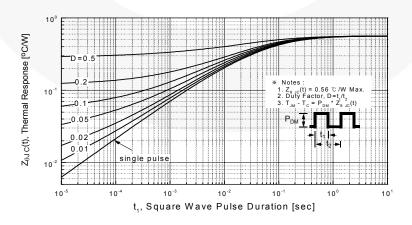


Figure 11. Transient Thermal Response Curve



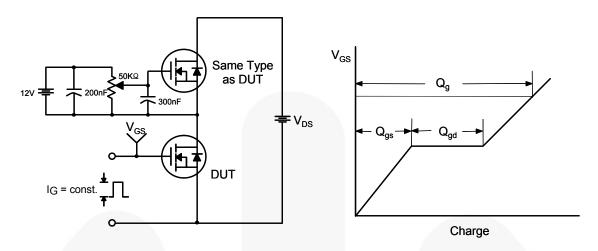


Figure 12. Gate Charge Test Circuit & Waveform

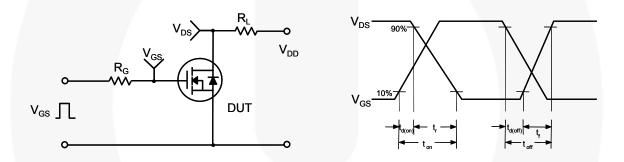


Figure 13. Resistive Switching Test Circuit & Waveforms

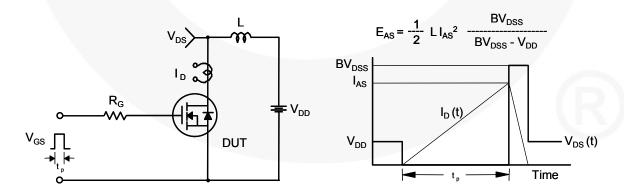


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

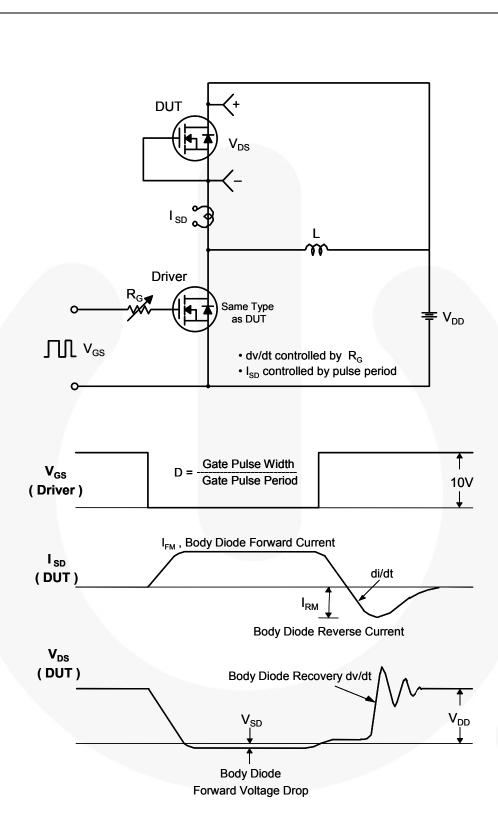
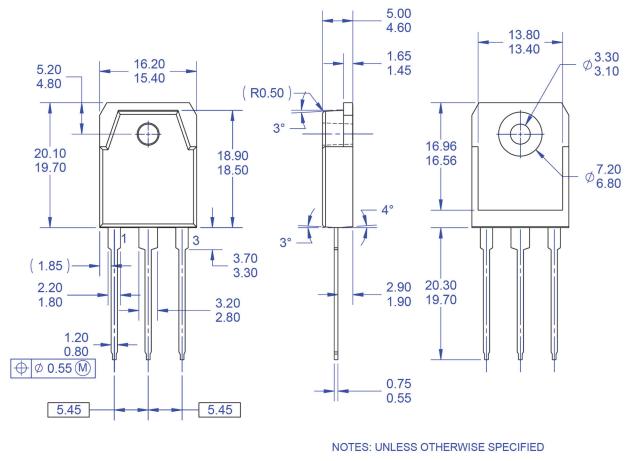
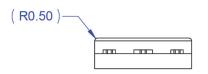


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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